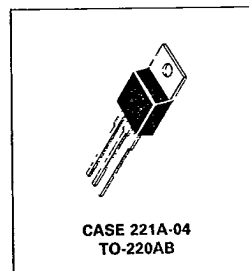
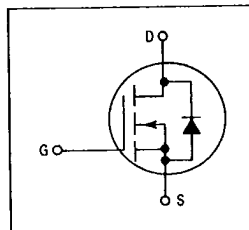


MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA
Designer's Data Sheet
Power Field Effect Transistor
**N-Channel Enhancement-Mode
Silicon Gate TMOS**

These TMOS Power FETs are designed for medium voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.

- Silicon Gate for Fast Switching Speeds — Switching Times Specified at 100°C
- Designer's Data — I_{DSS} , $V_{DS(on)}$, $V_{GS(th)}$ and SOA Specified at Elevated Temperature
- Rugged — SOA is Power Dissipation Limited
- Source-to-Drain Diode Characterized for Use With Inductive Loads


MTP10N35
MTP10N40
TMOS POWER FETs
10 AMPERES
 $r_{DS(on)} = 0.55 \text{ OHM}$
350 and 400 VOLTS

MAXIMUM RATINGS

Rating	Symbol	MTP		Unit
		10N35	10N40	
Drain-Source Voltage	V_{DSS}	350	400	Vdc
Drain-Gate Voltage ($R_{GS} = 1 \text{ M}\Omega$)	V_{DGR}	350	400	Vdc
Gate-Source Voltage — Continuous — Non-repetitive ($t_p \leq 50 \mu s$)	V_{GS} V_{GSM}	± 20 ± 40		Vdc Vpk
Drain Current Continuous Pulsed	I_D I_{DM}	10 40		Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	125 1		Watts W/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to 150		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	1 62.5	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	275	$^\circ\text{C}$

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

MOTOROLA TMOS POWER MOSFET DATA

3-704

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ($V_{GS} = 0, I_D = 0.25 \text{ mA}$)	$V_{(BR)DSS}$	350 400	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = \text{Rated } V_{DSS}, V_{GS} = 0$) ($V_{DS} = 0.8 \text{ Rated } V_{DSS}, V_{GS} = 0, T_J = 125^\circ\text{C}$)	I_{DSS}	—	0.2 1	mAdc
Gate-Body Leakage Current, Forward ($V_{GSF} = 20 \text{ Vdc}, V_{DS} = 0$)	I_{GSSF}	—	100	nAdc
Gate-Body Leakage Current, Reverse ($V_{GSR} = 20 \text{ Vdc}, V_{DS} = 0$)	I_{GSSR}	—	100	nAdc

ON CHARACTERISTICS*

Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 1 \text{ mA}$) $T_J = 100^\circ\text{C}$	$V_{GS(th)}$	2 1.5	4.5 4	Vdc
Static Drain-Source On-Resistance ($V_{GS} = 10 \text{ Vdc}, I_D = 5 \text{ Adc}$)	$r_{DS(on)}$	—	0.55	Ohm
Drain-Source On-Voltage ($V_{GS} = 10 \text{ V}$) ($I_D = 10 \text{ Adc}$) ($I_D = 5 \text{ Adc}, T_J = 100^\circ\text{C}$)	$V_{DS(on)}$	—	6 4.75	Vdc
Forward Transconductance ($V_{DS} = 10 \text{ V}, I_D = 5 \text{ A}$)	g_{FS}	4	—	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	($V_{DS} = 25 \text{ V}, V_{GS} = 0,$ $f = 1 \text{ MHz}$) See Figure 11	C_{iss}	—	1600	pF
Output Capacitance		C_{oss}	—	350	
Reverse Transfer Capacitance		C_{rss}	—	150	

SWITCHING CHARACTERISTICS* ($T_J = 100^\circ\text{C}$)

Turn-On Delay Time	($V_{DD} = 25 \text{ V}, I_D = 0.5 \text{ Rated } I_D$ $R_{gen} = 50 \text{ ohms}$) See Figures 9, 13 and 14	$t_{d(on)}$	—	60	ns
Rise Time		t_r	—	150	
Turn-Off Delay Time		$t_{d(off)}$	—	200	
Fall Time		t_f	—	120	
Total Gate Charge	($V_{DS} = 0.8 \text{ Rated } V_{DSS},$ $I_D = \text{Rated } I_D, V_{GS} = 10 \text{ V}$) See Figure 12	Q_g	40 (Typ)	60	nC
Gate-Source Charge		Q_{gs}	20 (Typ)	—	
Gate-Drain Charge		Q_{gd}	20 (Typ)	—	

SOURCE DRAIN DIODE CHARACTERISTICS*

Forward On-Voltage	($I_S = \text{Rated } I_D$ $V_{GS} = 0$)	V_{SD}	1.1 (Typ)	2	Vdc
Forward Turn-On Time		t_{on}	Limited by stray inductance		
Reverse Recovery Time		t_{rr}	600 (Typ)	—	ns

INTERNAL PACKAGE INDUCTANCE

Internal Drain Inductance (Measured from the contact screw on tab to center of die) (Measured from the drain lead 0.25" from package to center of die)	L_d	3.5 (Typ) 4.5 (Typ)	—	nH
Internal Source Inductance (Measured from the source lead 0.25" from package to source bond pad.)	L_s	7.5 (Typ)	—	

*Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

TYPICAL ELECTRICAL CHARACTERISTICS

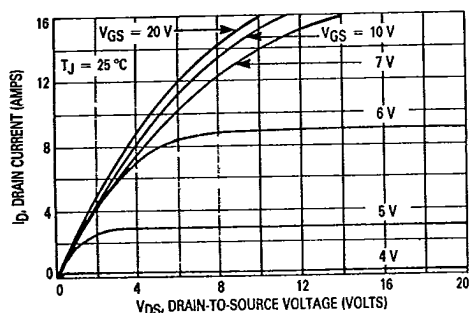


Figure 1. On-Region Characteristics

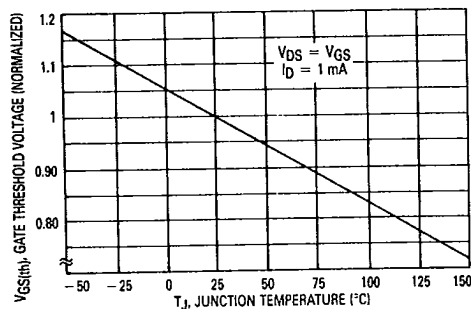


Figure 2. Gate-Threshold Voltage Variation With Temperature

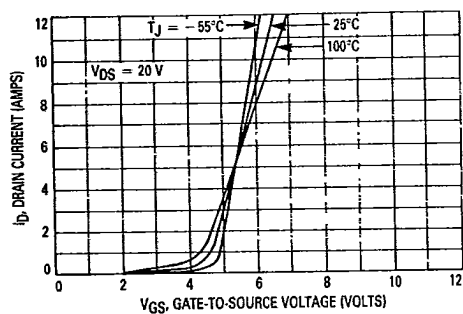


Figure 3. Transfer Characteristics

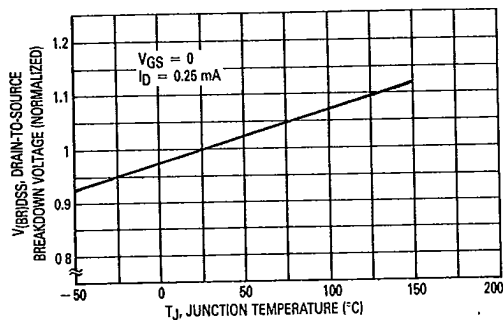


Figure 4. Breakdown Voltage Variation With Temperature

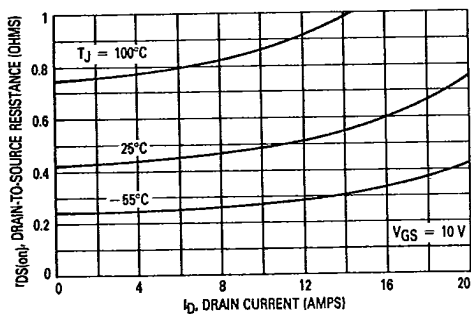


Figure 5. On-Resistance versus Drain Current

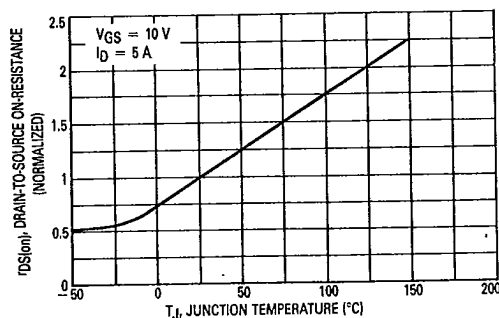


Figure 6. On-Resistance Variation With Temperature

MOTOROLA TMOS POWER MOSFET DATA

3-706

SAFE OPERATING AREA INFORMATION

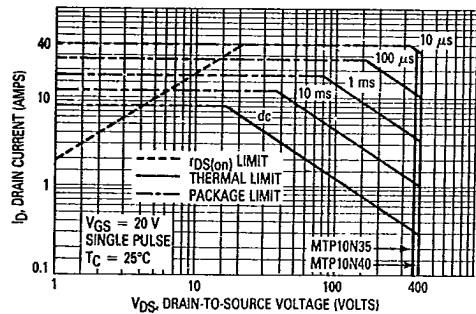


Figure 7. Maximum Rated Forward Biased Safe Operating Area

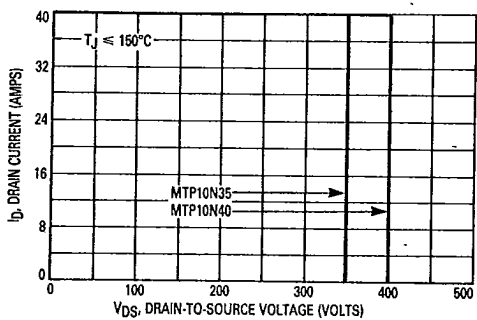


Figure 8. Maximum Rated Switching Safe Operating Area

FORWARD BIASED SAFE OPERATING AREA

The FBSOA curves define the maximum drain-to-source voltage and drain current that a device can safely handle when it is forward biased, or when it is on, or being turned on. Because these curves include the limitations of simultaneous high voltage and high current, up to the rating of the device, they are especially useful to designers of linear systems. The curves are based on a case temperature of 25°C and a maximum junction temperature of 150°C. Limitations for repetitive pulses at various case temperatures can be determined by using the thermal response curves. Motorola Application Note, AN569, "Transient Thermal Resistance-General Data and Its Use" provides detailed instructions.

SWITCHING SAFE OPERATING AREA

The switching safe operating area (SOA) of Figure 8 is the boundary that the load line may traverse without incurring damage to the MOSFET. The fundamental limits are the peak current, IDM and the breakdown voltage, V(BR)DSS. The switching SOA shown in Figure 8 is applicable for both turn-on and turn-off of the devices for switching times less than one microsecond.

The power averaged over a complete switching cycle must be less than:

Equation: (TJ(max) - TC) / RθJC

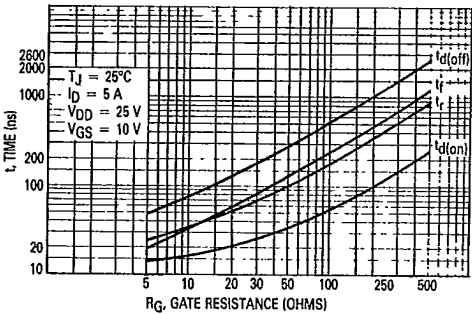


Figure 9. Resistive Switching Time Variation versus Gate Resistance

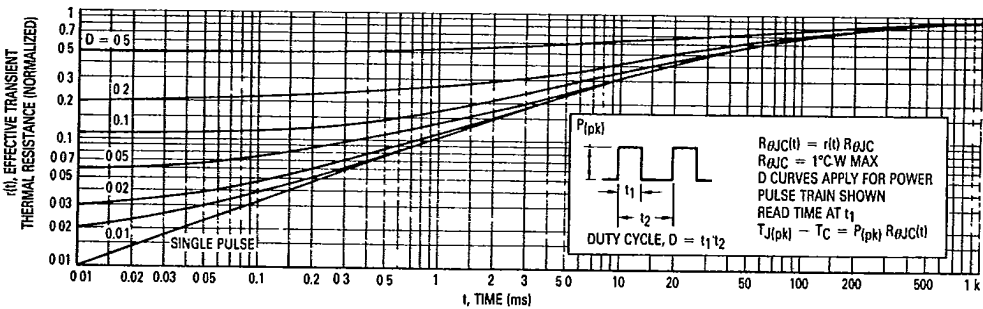


Figure 10. Thermal Response

MOTOROLA TMOS POWER MOSFET DATA

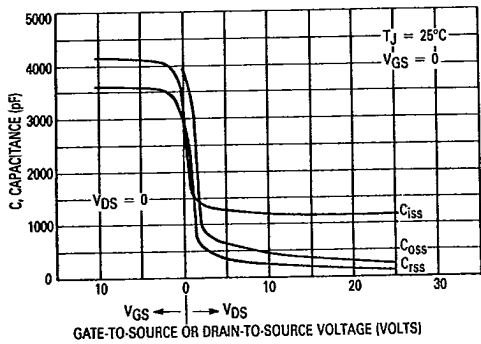


Figure 11. Capacitance Variation

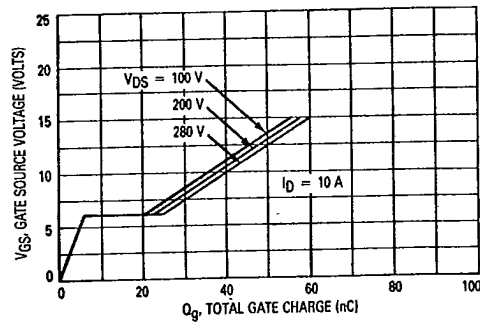


Figure 12. Gate Charge versus Gate-to-Source Voltage

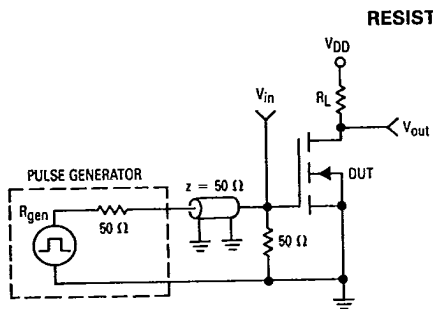


Figure 13. Switching Test Circuit

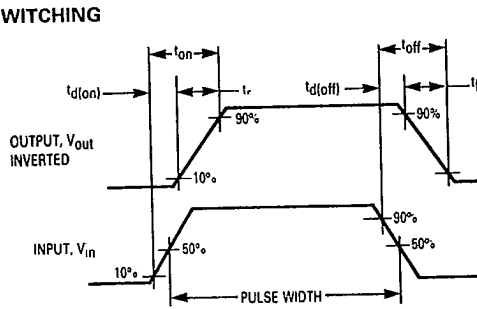
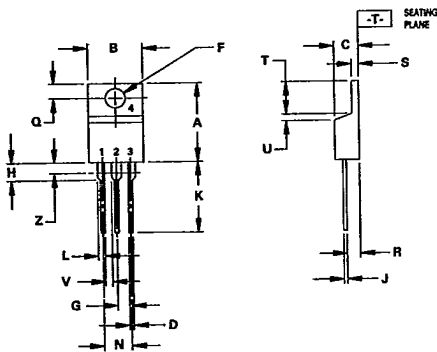


Figure 14. Switching Waveforms

OUTLINE DIMENSIONS



STYLE 5:
PIN 1, GATE
2, DRAIN
3, SOURCE
4, DRAIN

CASE 221A-04
TO-220AB

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	14.42	15.75	0.570	0.620
B	9.68	10.28	0.380	0.405
C	4.07	4.82	0.160	0.190
D	0.64	0.98	0.025	0.039
F	3.81	3.73	0.142	0.147
G	2.42	2.66	0.095	0.105
H	2.80	3.93	0.110	0.155
J	0.35	0.55	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.15	1.39	0.045	0.055
N	4.83	5.33	0.190	0.210
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.15	1.39	0.045	0.055
T	5.97	6.47	0.235	0.255
U	0.00	1.27	0.000	0.050
V	1.15	—	0.045	—
Z	—	2.04	—	0.080

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIM Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.